

SEMICONDUCTOR STRUCTURE AND METHOD FOR MANUFACTURING SAME

ABSTRACT

Embodiments of the disclosure provide a semiconductor structure and a method for manufacturing the same. The semiconductor structure includes a substrate, a first isolation trench located in the substrate, a first insulating layer covering a bottom surface and a lower part of a sidewall of the first isolation trench, a second insulating layer covering an upper part of the sidewall of the first isolation trench, and a third insulating layer at least partially located between the first insulating layer and the second insulating layer to isolate the first insulating layer from the second insulating layer.

[Fig. 2]